

## UNISONIC TECHNOLOGIES CO., LTD

UT6P02 Preliminary Power MOSFET

# -6.0A, -20V P-CHANNEL POWER MOSFET

#### ■ DESCRIPTION

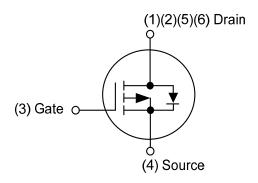
The UTC **UT6P02** is a P-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance and low gate charge, etc.

The UTC **UT6P02** is suitable for load switch and battery protection applications.

#### ■ FEATURES

- \*  $R_{DS(ON)} \le 33 \text{ m}\Omega$  @  $V_{GS}$ =-4.5V,  $I_{D}$ =-3.0A  $R_{DS(ON)} \le 50 \text{ m}\Omega$  @  $V_{GS}$ =-2.5V,  $I_{D}$ =-3.0A
- \* Improved dv/dt capability
- \* Fast switching
- \* Suit for -1.8V gate drive applications

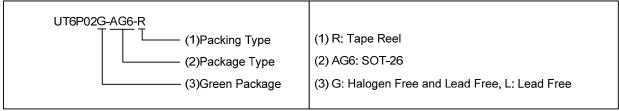
#### ■ SYMBOL



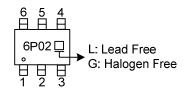
### ■ ORDERING INFORMATION

Ordering Number		Daakaaa	Pin Assignment					Da akina		
Lead Free	Halogen Free	Package	1	2	3	4	5	6	Packing	
UT6P02L-AG6-R	UT6P02G-AG6-R	SOT-26	D	D	G	S	D	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



#### MARKING



<u>www.unisonic.com.tw</u> 1 of 5

## ■ ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		$V_{DSS}$	-20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±8	V	
Drain Current	Continuous	I <sub>D</sub>	-6	Α	
	Pulsed (Note 2)	I <sub>DM</sub>	-12	Α	
Avalanche Energy	Single Pulsed (Note 3)	E <sub>AS</sub>	33	mJ	
Power Dissipation		$P_D$	1.38	W	
Junction Temperature		TJ	+150	°C	
Storage Temperature		T <sub>STG</sub>	-55 ~ +150	°C	

- Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

  Absolute maximum ratings are stress ratings only and functional device operation is not implied.
  - 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
  - 3. L=0.1mH,  $I_{AS}$ =-25A,  $V_{DD}$ =-15V,  $R_{G}$ =25  $\Omega$ , Starting  $T_{J}$  = 25°C

#### ■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	$\theta_{JA}$	90	°C/W

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

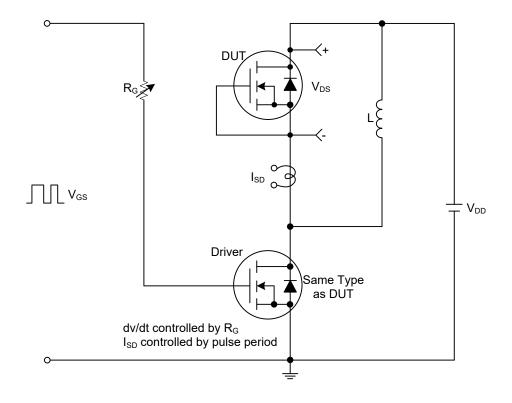
## ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

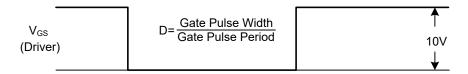
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D$ =-250 $\mu$ A, $V_{GS}$ =0 $V$	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-20V, $V_{GS}$ =0V			-1	μΑ
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}$ =±8 $V$ , $V_{DS}$ =0 $V$			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$ , $I_{D}=-250\mu A$	-0.3		-1.0	V
Static Drain-Source On-State Resistance	В	$V_{GS}$ =-4.5V, $I_{D}$ =-4.5A			33	mΩ
Static Dialii-Source Oil-State Resistance	R <sub>DS(ON)</sub>	$V_{GS}$ =-2.5V, $I_{D}$ =-4.5A			50	mΩ
DYNAMIC PARAMETERS						
Input Capacitance	$C_{ISS}$			1450		рF
Output Capacitance	Coss	V <sub>GS</sub> =0V, V <sub>DS</sub> =-10V, f=1.0MHz		350		рF
Reverse Transfer Capacitance	$C_{RSS}$			305		рF
SWITCHING PARAMETERS						_
Total Gate Charge	$Q_{G}$	1/ 10)/ )/ 15)/ 1 0 0 0		18		nC
Gate to Source Charge	$Q_GS$	V <sub>DS</sub> =-16V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-6.0A (Note 1, 2)		3		nC
Gate to Drain Charge	$Q_GD$	(Note 1, 2)		5.2		nC
Turn-ON Delay Time	$t_{D(ON)}$			9		ns
Turn-ON Rise Time	$t_R$	V <sub>DD</sub> =-10V, V <sub>GS</sub> =-4.5V,		20		ns
Turn-OFF Delay Time	$t_{D(OFF)}$	I <sub>D</sub> =-6.0A, R <sub>G</sub> =3.3Ω (Note 1, 2)		45		ns
Turn-OFF Fall-Time	t <sub>F</sub>			36		ns
SOURCE- DRAIN DIODE RATINGS AND	CHARACTE	RISTICS	_	_	_	
Maximum Body-Diode Continuous					_	^
Current	Is				-6	Α
Maximum Body-Diode Pulsed Current	I <sub>SM</sub>				-12	Α
Diode Forward Voltage	$V_{\text{SD}}$	I <sub>S</sub> =-1.0A,V <sub>GS</sub> =0V			-1.2	V

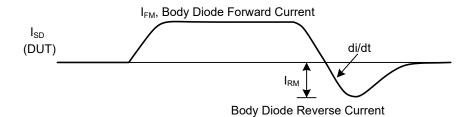
Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%.

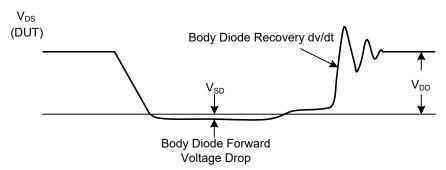
2. Essentially independent of operating temperature.

## TEST CIRCUITS AND WAVEFORMS



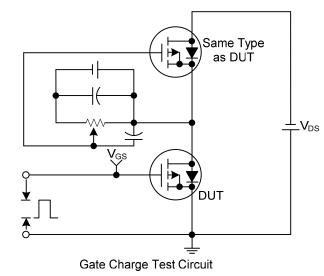


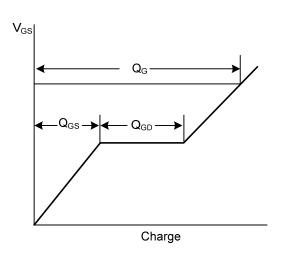




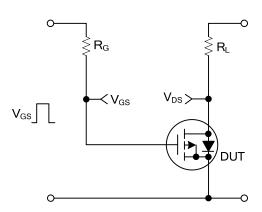
Peak Diode Recovery dv/dt Test Circuit and Waveforms

## ■ TEST CIRCUITS AND WAVEFORMS

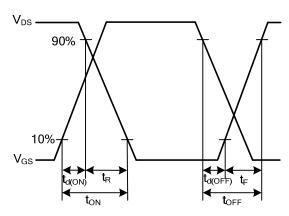




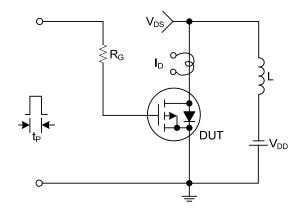
Gate Charge Waveforms



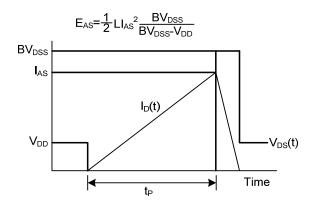
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. UTC reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Preliminary**